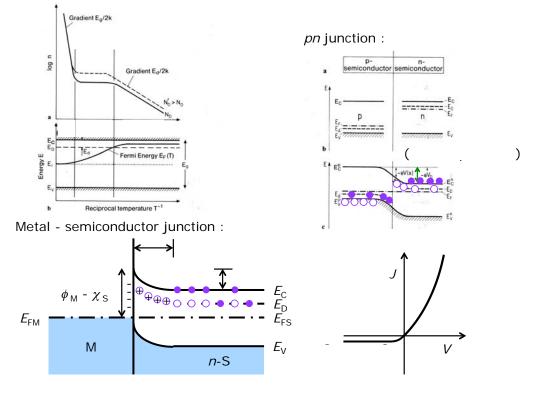


Temperature dependence of an extrinsic semiconductor :





Y

Contents of Introductory Nanotechnology

First half of the course :

Basic condensed matter physics

- 1. Why solids are solid?
- 2. What is the most common atom on the earth?
- 3. How does an electron travel in a material ?
- 4. How does lattices vibrate thermally ?
- 5. What is a semi-conductor ?

6. How does an electron tunnel through a barrier ?

- 7. Why does a magnet attract / retract ?
- 8. What happens at interfaces ?

Second half of the course :

Introduction to nanotechnology (nano-fabrication / application)

How Does an Electron Tunnel through a Barrier ?

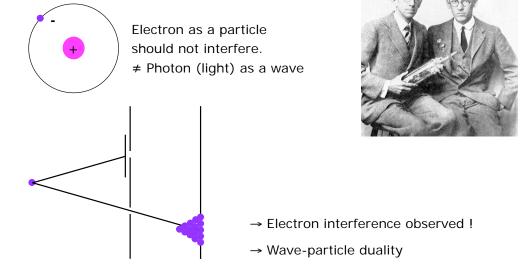
- De Broglie wave
- Schrödinger equation
 - 1D quantum well
 - Quantum tunneling
- Reflectance / transmittance
 - Optical absorption
 - Direct / indirect band gap

Electron Interference

Davisson-Germer experiment in 1927 :

Y

Electrons are introduced to a screen through two slits.



Scrödinger's Cat

Thought experiment proposed by E. Schrödinger in 1935





The observer cannot know

- if a radioactive atom has decayed.
- if the vial has been broken and the hydrocyanic acid has been released.
- if the cat killed.

Y

 \rightarrow The cat is both dead and alive according to quantum law : superposition of states

The superposition is lost :

- only when the observer opens the box and learn the condition of the cat.
- then, the cat becomes dead or alive.
- → quantum indeterminacy

* http://www.wikipedia.org/

De Broglie Wave

Wave packet :

contains number of waves, of which amplitude describes probability of the presence of a particle.

$$\lambda = \frac{h}{m_0 v}$$

where λ : wave length, *h*: Planck constant and m_0 : mass of the particle.

→ de Broglie hypothesis (1924 PhD thesis → 1929 Nobel prize)

(1924 PhD thesis \rightarrow 1929 Nobel prize)

According to the mass-energy equivalence :

$$E = m_0 c^2 = m_0 c \cdot c = p \cdot \lambda v$$

where p: momentum and v: frequency. By using E = hv,

$$\lambda = \frac{h}{p} = \frac{h}{m_0 v}$$





* http://www.wikipedia.org/

In order to express the de Broglie wave, Schrödinger equation is introduced in 1926 :

$$\frac{\hbar^2}{2m}\nabla^2\psi + (E - V)\psi = 0 \qquad \left(\nabla^2 = \frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} + \frac{\partial^2}{\partial z^2}\right)$$

E : energy eigenvalue and ψ : wave function

Wave function represents probability of the presence of a particle $\left|\psi\right|^2$ = $\psi^*\psi$

 ψ^* : complex conjugate (*e.g.*, z = x + iy and $z^* = x - iy$)

Propagation of the probability (flow of wave packet) :

$$j = \frac{\hbar}{2mi} \left(\psi^* \nabla \psi - \psi \nabla \psi^* \right)$$

Operation = observation :

de Broglie wave

$$-\frac{\hbar^2}{2m}\nabla^2 \psi = (E - V)\psi$$
observed results

Y.

1D Quantum Well Potential

A de Broglie wave (particle with mass m_0) confined in a square well :

$$\begin{cases} \frac{\hbar^2}{2m_0} \frac{d^2\psi_1}{dx^2} + (E - V_0)\psi_1 = 0 & (x < -a) \\ \frac{\hbar^2}{2m_0} \frac{d^2\psi_2}{dx^2} + E\psi_2 = 0 & (-a < x < a) \\ \frac{\hbar^2}{2m_0} \frac{d^2\psi_3}{dx^2} + (E - V_0)\psi_3 = 0 & (a < x) \end{cases}$$

х

General answers for the corresponding regions are

$$\begin{cases} \psi_1 = Ce^{\beta x} + C_1 e^{-\beta x} & (x < -a) \\ \psi_2 = A \sin \alpha x + B \cos \alpha x & (-a < x < a) \\ \psi_3 = De^{-\beta x} + D_1 e^{\beta x} & (a < x) \end{cases} \qquad \begin{cases} \alpha = \frac{\sqrt{2m_0 E}}{\hbar} \\ \beta = \frac{\sqrt{2m_0 (V_0 - E)}}{\hbar} \end{cases}$$

Since the particle is confined in the well, $\psi_1, \psi_3 \to 0 \quad (x \to \pm \infty)$

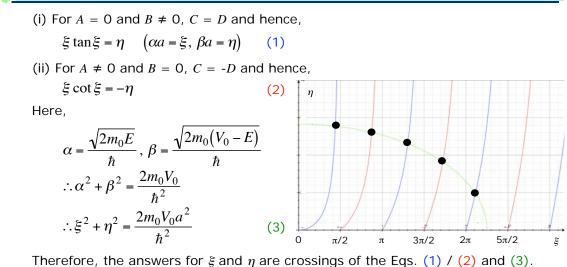
For $E < V_0$, $C_1 = 0, D_1 = 0$

Y

Boundary conditions :

At x = -a, to satisfy $\psi_1 = \psi_2$, $-A \sin \alpha a + B \cos \alpha a = Ce^{-\beta a}$ $\psi_1' = \psi_2'$, $\alpha A \cos \alpha a + \alpha B \sin \alpha a = \beta Ce^{-\beta a}$ At x = a, to satisfy $\psi_2 = \psi_3$, $A \sin \alpha a + B \cos \alpha a = De^{-\beta a}$ $\psi_2' = \psi_3'$, $\alpha A \cos \alpha a - \alpha B \sin \alpha a = -\beta De^{-\beta a}$ $2A \sin \alpha a = (D - C)e^{-\beta a}$ $2\alpha A \cos \alpha a = -\beta (D - C)e^{-\beta a}$ $2aA \cos \alpha a = -\beta (D - C)e^{-\beta a}$ $2aB \sin \alpha a = \beta (C + D)e^{-\beta a}$ For $A \neq 0$, $D - C \neq 0$: $\alpha \cot \alpha a = -\beta$ For $B \neq 0$, $D + C \neq 0$: $\alpha \tan \alpha a = \beta$ For both $A \neq 0$ and $B \neq 0$: $\tan^2 \alpha a = -1 \Rightarrow \alpha$: imaginary number Therefore, either $A \neq 0$ or $B \neq 0$.

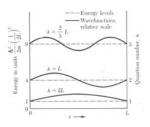
1D Quantum Well Potential (Cont'd)



Energy eigenvalues are also obtained as

$$E = \frac{\hbar^2}{2m_0 a^2} \xi^2$$

→ Discrete states



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In classical theory,

Particle with smaller energy than the potential barrier

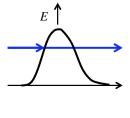
cannot pass through the barrier.

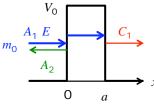
In quantum mechanics, such a particle have probability to tunnel.

For a particle with energy $E (< V_0)$ and mass $m_{0'}$

Schrödinger equations are

$$\begin{cases} \frac{\hbar^2}{2m_0} \frac{d^2 \psi}{dx^2} + E\psi = 0 & (x < 0, a < x) \\ \frac{\hbar^2}{2m_0} \frac{d^2 \psi}{dx^2} + (E - V_0)\psi = 0 & (0 < a < x) \end{cases}$$





Substituting general answers $k_1 = \sqrt{2m_0E}/\hbar$, $k_2 = \sqrt{2m_0(V_0 - E)}/\hbar$ $\left[\psi = A_1 \exp(ik_1x) + A_2 \exp(-ik_1x)\right]$ (x < 0)

$$\begin{cases}
\psi = B_1 \exp(k_2 x) + B_2 \exp(-k_2 x) & (0 < a < x) \\
\psi = C_1 \exp(ik_1 x) + C_2 \exp(-ik_1 x) & (a < x)
\end{cases}$$

Y.

Quantum Tunneling (Cont'd)

Now, boundary conditions are

$$\begin{cases} A_{1} + A_{2} = B_{1} + B_{2}, & ik_{1}(A_{1} - A_{2}) = k_{2}(B_{1} - B_{2}) & (x = 0) \\ B_{1} \exp(k_{2}a) + B_{2} \exp(-k_{2}a) = C_{1} \exp(ik_{1}a), & k_{2}[B_{1} \exp(k_{2}a) - B_{2} \exp(-k_{2}a)] = ik_{1}C_{1} \exp(ik_{1}a) & (x = a) \\ \\ \vdots & \begin{cases} \frac{C_{1}}{A_{1}} = \frac{4ik_{1}k_{2} \exp(-ik_{1}a)}{(k_{2} + ik_{1})^{2} \exp(-k_{2}a) - (k_{2} - ik_{1})^{2} \exp(k_{2}a)} \\ \\ \frac{A_{2}}{A_{1}} = \frac{(k_{1}^{2} + k_{2}^{2})[\exp(k_{2}a) - \exp(-k_{2}a)]}{(k_{2} - ik_{1})^{2} \exp(-k_{2}a) - (k_{2} + ik_{1})^{2} \exp(k_{2}a)} \end{cases}$$

Now, transmittance T and reflectance R are

$$\begin{cases} T = \left| \frac{C_1}{A_1} \right|^2 = \frac{4k_1^2 k_2^2}{\left(k_1^2 + k_2^2\right)^2 \sinh^2(k_2 a) + 4k_1^2 k_2^2} = \frac{4E(V_0 - E)}{V_0^2 \sinh^2(a/2b) + 4E(V_0 - E)} \\ \\ R = \left| \frac{A_2}{A_1} \right|^2 = \frac{\left(k_1^2 + k_2^2\right)^2 \sinh^2(k_2 a)}{\left(k_1^2 + k_2^2\right)^2 \sinh^2(k_2 a) + 4k_1^2 k_2^2} = \frac{V_0 \sinh^2(a/2b)}{V_0^2 \sinh^2(a/2b) + 4E(V_0 - E)} \\ \\ \left(b = \frac{\hbar}{2\sqrt{2m_0(V_0 - E)}} \right) \qquad \rightarrow T \neq 0 \text{ (tunneling occurs) !} \end{cases}$$

For
$$V_0 - E \gg \hbar^2 / 2m_0 a^2$$

 $\therefore \hbar / a \ll \sqrt{2m_0(V_0 - E)}, a/2b \gg 1$
 $\therefore V_0^2 \sinh^2(a/2b) + 4E(V_0 - E) \approx V_0^2 \sinh^2(a/2b) \approx V_0^2 \exp(a/b) \approx V_0^2 \exp\left(\frac{2\sqrt{2m_0(V_0 - E)}a}{\hbar}\right)$
 $\therefore T \approx \frac{4E(V_0 - E)}{V_0^2} \exp\left(-\frac{2\sqrt{2m_0(V_0 - E)}a}{\hbar}\right) \Rightarrow T$ exponentially decrease with increasing *a* and $(V_0 - E)$
For $V_0 < E$, as k_2 becomes an imaginary number, $m_0 \xrightarrow{E} V_0$

$$k_{2}' = \frac{\sqrt{2m_{0}(E - V_{0})}}{\hbar} \left(k_{2} \rightarrow ik_{2}'\right)$$

$$\begin{cases}
T = \frac{4k_{1}^{2}k_{2}'^{2}}{\left(k_{1}^{2} - k_{2}'^{2}\right)^{2}\sin^{2}\left(k_{2}'a\right) + 4k_{1}^{2}k_{2}'^{2}} = \frac{4E(E - V_{0})}{V_{0}^{2}\sin^{2}\left(k_{2}'a\right) + 4E(E - V_{0})} \quad 0 \quad a \end{cases} \times \\
R = \frac{\left(k_{1}^{2} + k_{2}'^{2}\right)^{2}\sin^{2}\left(k_{2}'a\right)}{\left(k_{1}^{2} + k_{2}'^{2}\right)^{2}\sin^{2}\left(k_{2}'a\right) + 4k_{1}^{2}k_{2}'^{2}} = \frac{V_{0}\sin^{2}\left(k_{2}'a\right)}{V_{0}^{2}\sin^{2}\left(k_{2}'a\right) + 4E(E - V_{0})} \quad \Rightarrow R \neq 0 !$$

Reflectance and Transmittance

At an energy level *E*, wave function is expressed as $\psi = \varphi(x) \exp(-iEt/\hbar)$

$$\begin{split} |\psi|^2 &= |\varphi(x)|^2 \qquad \therefore \frac{\partial |\psi|^2}{\partial t} = \frac{\partial |\varphi(x)|^2}{\partial t} = 0\\ \text{According to the equation of continuity} : \quad \frac{\partial \rho}{\partial t} + \text{div } \boldsymbol{j} = 0 \qquad \left(\text{div } \boldsymbol{j} = \frac{\partial j_x}{\partial x} + \frac{\partial j_y}{\partial y} + \frac{\partial j_z}{\partial z} \right)\\ \text{div } \boldsymbol{j} = 0\\ \text{For 1D,} \quad \frac{d j_x}{d x} = 0 \qquad \therefore \boldsymbol{j} = \boldsymbol{j}_x = \text{const.} \end{split}$$

At the incident side, the incident wave $\psi_{\rm i}$ and the reflection wave $\psi_{\rm r}$ satisfy

$$\begin{split} \psi &= \psi_{i} + \psi_{r} \qquad \therefore j = j_{i} + \left| j_{r} \right| \\ \text{Here,} \quad j &= \frac{\hbar}{2m_{0}i} \left(\psi^{*}\psi' - \psi\psi^{*'} \right), \ j_{i} = \frac{\hbar}{2m_{0}i} \left(\psi_{i}^{*}\psi_{i}' - \psi_{i}\psi_{i}^{*'} \right), \ j_{r} = \frac{\hbar}{2m_{0}i} \left(\psi_{r}^{*}\psi_{r}' - \psi_{r}\psi_{r}^{*'} \right) \end{split}$$

At the transmission side, only the transmission wave ψ_t exists, and thus $j = j_t$

$$\therefore j_{i} + |j_{r}| = j_{t} \qquad \therefore j_{i} = j_{t} + |j_{r}|$$

$$\therefore 1 = \frac{j_{t}}{j_{i}} + \frac{|j_{r}|}{j_{i}} \qquad \therefore 1 = T + R$$

$$\rightarrow T : \text{ transmittance and } R : \text{ reflectance}$$

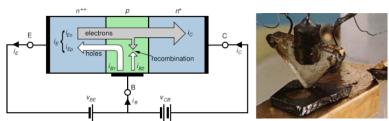
$$(j_{t} \neq j_{i}) \qquad (|j_{r}| \neq j_{i})$$



You

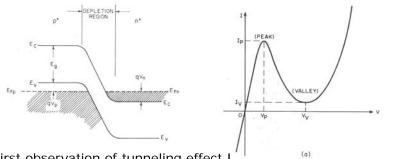
Transistor and Esaki Diode

First bipolar transistor (transfer resistor) was invented by J. Bardeen , W. Shockley and W. Brattainin 1947 :





Tunneling diode was invented by L. Esaki in 1958 :



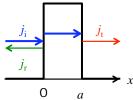


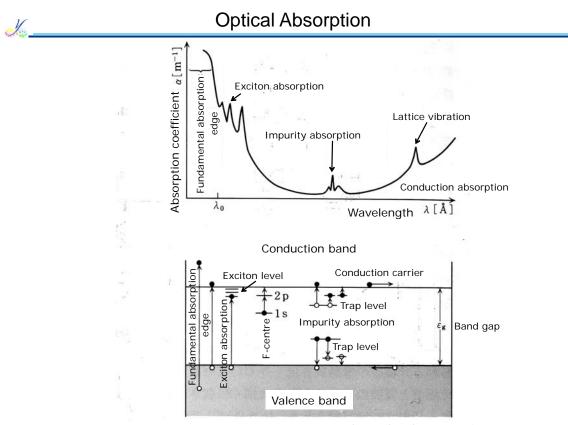
→ First observation of tunneling effect !

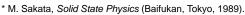
* http://www.wikipedia.org/; http://photos.aip.org/; ** S. M. Sze, *Physics of Semiconductor Devices* (John Wiley, New York, 1981).

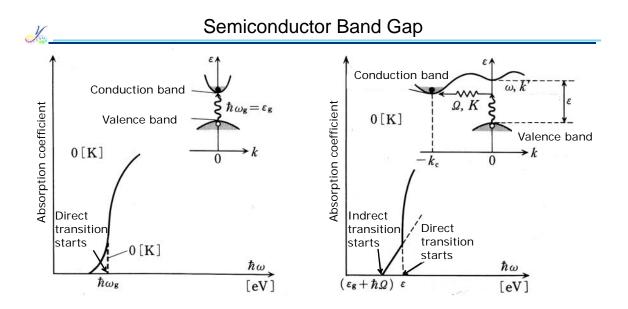
Absorption Coefficient

Absorption fraction A is defined as A + R + T = 1Here, $j_r = Rj_i$, and therefore $(1 - R) j_i$ is injected. Assuming j at x becomes j - dj at x + dx, $-dj = \alpha j dx$ (α : absorption coefficient) With the boundary condition : at x = 0, $j = (1 - R) j_i$, $j = (1 - R)j_i \exp(-\alpha x)$ With the boundary condition : x = a, $j = (1 - R) j_i e^{-\alpha a}$, part of which is reflected ; $R (1 - R) j_i e^{-\alpha a}$ and the rest is transmitted ; $j_t = [1 - R - R (1 - R)] j_i e^{-\alpha a}$ $j_t = (1 - R)^2 j_i \exp(-\alpha x)$ $\therefore T = \frac{j_t}{j_i} = (1 - R)^2 \exp(-\alpha x)$









Excited electrons will be recombine with holes with emitting photon. → Light emitting diode (LED)

* M. Sakata, Solid State Physics (Baifukan, Tokyo, 1989).

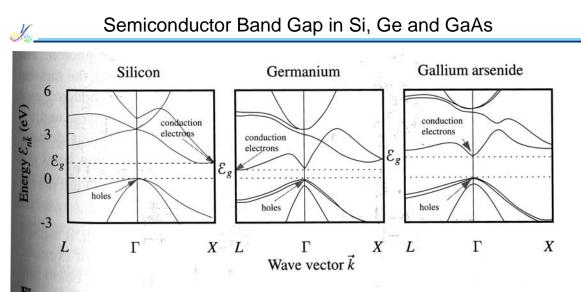


Figure 19.8. Essential features of band structures of silicon, germanium, and gallium arsenide. All have band gaps on the order of 1 eV. The bottom of the conduction band for silicon and germanium does not lie at Γ , so these materials have an indirect gap. Gallium arsenide, by contrast, has a direct gap. These diagrams are extracted from Figures 23.15 and 23.16, which contain information on how they were obtained.

* M. P. Marder, Condensed Matter Physics (John-Wiley, New York, 2000).

